Application Note Parallel Operation of TPS2663 eFuses

TEXAS INSTRUMENTS

Rakesh Panguloori

Power Switches

ABSTRACT

The TPS2663 is a 6-A industrial eFuse which provides robust power path protection with Class-A system performance in systems such as PLCs, Industrial PCs, Control and Automation and Sensors. Some applications such as field power supply feeding multiple I/O modules or an I/O-link master module require higher current protection than 6-A supported by the TPS2663 eFuse. Traditionally, hot-swap and ORing controllers with external MOSFETs are used for high current needs with a compromise on the system performance. This application report covers the parallel operation of TPS2663 eFuses to achieve robust protection at higher output currents. An example of paralleling four TPS2663 devices is considered to describe the design considerations and to demonstrate the performance during the system transients. Detailed comparison between the hot-swap and ORing controller-based solution and the eFuse solution is presented.

Table of Contents

1 Introduction	2
2 Parallel Configuration	3
3 Design Example	6
3.1 Design Requirements	6
3.2 Detailed Design Procedure	6
3.3 Performance Results	8
4 Comparison With the Hot-Swap and ORing Controller Solution	11
5 TPS16630 Parallel Circuit Configuration	
6 Conclusion	
7 References	

Trademarks

All trademarks are the property of their respective owners.

1



1 Introduction

The TPS2663 device incorporates protection features such as inrush current management, adjustable overcurrent limit, short-circuit protection, overvoltage and input reverse polarity protection. Figure 1-1 shows an application schematic of the TPS26631 feeding a downstream DC-DC converter in a PLC system. The capacitor C_{dVdT} on the dVdT pin sets the output voltage slew-rate and hence the inrush current level where as the resistor R_{ILIM} sets the current limit (ILIM) which the device needs to limit to under fault conditions. The device offers a B-FET driver to control an external N-channel FET 'Q1' for reverse current and reverse polarity protection which simplifies designs requiring class-A performance during system tests like IEC61000-4-5 surge tests as well as input supply brown-out tests.

The maximum current the TPS2663 can support is up to 6 A. However the device can be used in parallel configuration with multiple TPS2663 devices to achieve higher output currents which is often required in many industrial systems. This report presents how the TPS2663 can be used in parallel operation to achieve higher output currents as well as to demonstrate the performance benefits it brings to the system with its integrated protection functions.



Figure 1-1. Application Schematic of TPS26631 for Power Path Protection in a PLC System



2 Parallel Configuration

The basic principle of eFuse parallel operation and the design considerations are covered in the *Achieve 20-A Circuit Protection and Space Efficiency Using Paralleled eFuses* Application Report⁽¹⁾. The same concept is applicable for TPS26631 parallel operation. The key points from the *Achieve 20-A Circuit Protection and Space Efficiency Using Paralleled eFuses* Application Report⁽¹⁾ are summarized in the rest of this section in the context of TPS26631.

- During start-up, equal current sharing among the parallel-connected eFuses is needed to ensure successful start-up. To achieve that,
 - The UVLO, OVP, SHDNb pins of all the parallel-connected eFuses are connected together for synchronizing the ON or OFF operation
 - The dVdT pins of all the eFuses are connected together to ensure uniform output ramp rate and equal dynamic power stress
- During steady-state operation, the current sharing is decided by the R_{DS(on)} mismatch. The device having the lower R_{DS(on)} shares more current than the rest of the devices. However, the self-heating effect due to positive temperature characteristics of the MOSFET helps to a larger extent towards equal load current distribution in parallel configuration.
- During overload operation, the inherent current source characteristic of eFuse forces all the parallelconnected eFuses to operate in current-limiting mode. For the TPS26631, each device should have its own current-limiting resistor (R_{ILIM}) as demanded by the internal current loop architecture.



Figure 2-1. Circuit Configuration of Two TPS26631 Devices in Parallel





Figure 2-2. Current Sharing Between the Devices During Start-up in dVdT mode

Figure 2-1 illustrates the circuit configuration of two TPS26631 devices in parallel. A single blocking FET Q_1 on the primary eFuse is enough for reverse current blocking. Figure 2-2 shows the current sharing during start-up with dVdT pins together. Even though the ramp rate of the dVdT pin is the same for both the devices, the mismatch in the internal dVdT gain and the internal FET characteristics leads to unequal current sharing during start-up. For uniform current distribution while starting up into large loads, current limited start-up is recommended as follows

- Leave dVdT pins OPEN
- Use R_{ILIM} resistor switch network at the ILIM pin. The R_{ILIM_Low} sets the inrush current. After successful start-up, PGOOD asserts high which sets the overload current limit as per (R_{ILIM_Low} || R_{ILIM_High}) at the ILIM pin

The modified parallel circuit configuration is illustrated in Figure 2-3 and the corresponding start-up waveform demonstrating equal start-up current between two TPS26631 devices is shown in Figure 2-4. In this application report, R_{ILIM} resistor switch network is considered in the design example as it ensures uniform current sharing under all the stressful events.





Figure 2-3. Parallel Configuration of TPS26631 With RILIM Switch Network at ILIM Pins



Figure 2-4. Current Sharing Between the Devices During Start-up in Current-Limit Mode



3 Design Example

An example of designing four TPS26631 eFuse parallel circuits is considered in this section.

3.1 Design Requirements

Table 3-1 shows the design parameters for this application example.

Design Parameter	Example Value		
Typical input voltage, V _{IN}	24 V		
Undervoltage lockout set point, V _{UV}	18 V		
Overvoltage cutoff set point, V _{OV}	33 V		
Inrush current limit, I _{INRUSH}	2.4 A		
Maximum load current, I _{OUT}	22 A		
IEC61000-4-5 Surge test level	±500 V with 2-Ω generator impedance		
Surge performance	Class-A		

Table 3-1. Design Parameters

3.2 Detailed Design Procedure

Device selection

In this example, the TPS26631 variant is considered to highlight the current sharing during the 2 × pulse current support. For more information, see the *Device Comparison Table* in the *TPS2663x 60-V, 6-A Power Limiting, Surge Protection Industrial eFuse* data sheet for device selection. In a system where reverse current blocking is not required, the TPS1663 devices are recommended.

ILIM setting

To limit the inrush current to 2.4 A (that is, 0.6 A per device), the R_{LIM_Low} is selected as 30 k Ω . Considering the cumulative current limit accuracy of 10% and to support maximum load current of 22 A, the current limit is set at 24 A (that is, 6 A per device). This results in 3.33-k Ω value for R_{LIM} High.

Undervoltage Lockout and Overvoltage Set Point

The resistors R1, R2, and R3 are selected as 887 k Ω , 29.4 k Ω , and 34 k Ω , respectively, to set 18 V as undervoltage lockout and 33 V as overvoltage trip point.

dVdT capacitor

Leave dVdT pins OPEN because the R_{ILIM} resistor switch network is considered in this design.

IMON resistor

In parallel configuration, IMON pins of all the devices can be combined to monitor the total system current. The maximum value of the R_{IMON} resistor can be determined by Equation 1. The maximum V_{IMON} voltage is determined by the ADC input range and it is 3.3 V.

$$V_{IMON} = \left[OUT_{max} \times GAIN_{IMON} \right] \times R_{IMON}$$

Where GAIN_{IMON} is 27.9 μ A/A (typ) and I_{OUT_max} is 48 A because of 2 × overcurrent pulse support with the TPS26631.

Using Equation 1, we get R_{IMON} as 2.46 k Ω .

PGOOD, FLTb

The output of these pins are used only from the primary eFuse to control downstream load and these pins are left OPEN for the rest of the parallel TPS26631 devices.

• PGTH

The TPS2663 device uses PGTH as the output load voltage monitor and to set the downstream loads UVLO threshold. The voltage at PGTH determines the way the TPS2663 recovers during the system faults. During the fault recovery instance, if the $V_{(PGTH)}$ level is above $V_{(PGTHF)}$, then the internal FET turns ON with a fast slew rate to meet Class-A system performance during surge events with optimal output buffer capacitance.

Typically, the minimum operating voltage of the DC-DC converter designed for 24-V rail is at 15 V. Assuming UVLO to be at 20% lower level, $V_{UVLO\ DC-DC}$ = 12 V. Use Equation 2 to calculate R₄ and R₅.

$$V_{(PGTHF)} = \frac{R_5}{R_4 R_5} \times V_{UVLO_DC-DC}$$
(2)

 $V_{(PGTHF)}$ = 1.14 V. Assuming R_5 = 56 k Ω , R_4 comes out to be approximately 499 k Ω .

Output Buffer Capacitor, C_{OUT}

During the surge event T_{SURGE} , the output capacitor C_{OUT} of the TPS2663 provides energy to the load. The C_{OUT} should be selected such that the output voltage does not drop below V_{UVLO_DC-DC} during T_{SURGE} interval. Use Equation 3 to compute the required buffer capacitor C_{OUT} :

$$C_{OUT} = \frac{2 \times P_{(D\hat{C} \ DC)} \times T_{SURGE}}{V_{(IN_SYS)}^2 \ V_{(UV_D\hat{C} \ DC)}^2}$$

(3)

where

- P_(DC-DC) = max load power ≈ 500 W
- T_{SURGE} ́≈1 ms
- V_(IN_SYS) = 24 V
- V_(UV_DC-DC) = 15 V

The value is determined to be C_{OUT} = 2.85 mF. Choose a capacitor with ±10% tolerance, C_{OUT} = 3 mF / 35 V electrolytic capacitor.

Input and output capacitors

A minimum of $0.1-\mu F$ ceramic decoupling capacitor is recommended at the input and the output for each of the eFuse.

Reverse current blocking FET

Choose at least a 80-V rated N-channel FET. Two CSD19532Q5B FETs are used in parallel to support continuous load current of 22 A.

TVS diode and Schottky diode

For clamping \pm 500-V, 2- Ω surge voltages with in the absolute maximum voltage rating of the TPS2663 device, bidirectional TVS diode SMCJ36CA is used at the input. Similarly, to clamp the negative voltages at the output during fast turn-off events, a Schottky diode B560C-13-F is recommended at the output.

7

3.3 Performance Results

Figure 3-1 shows the PCB with four TPS26631 devices.



Figure 3-1. Evaluation Board With Four TPS26631 Devices in Parallel



Figure 3-2. Turn-on Control With SHDN



Figure 3-3. Turn-off Control With SHDN





Figure 3-4. IMON Response During Load Current Step From 2 A to 20 A



Figure 3-6. Overload Performance During Load Current Step From 15 A to 28 A



Figure 3-8. Response During Recovery From Overload Fault



Figure 3-5. Current Sharing Between Two Devices During Load Current Step from 2 A to 20 A



Figure 3-7. Current Sharing Between Two Devices During Overload Fault



Figure 3-9. Response During Start-up With Short on Output



Figure 3-10. Response During Recovery From Output Short-Circuit



Figure 3-12. Response During Hot-Short at the Output



Figure 3-14. Voltage Interruption Response of Four TPS26630 Devices in Parallel Configuration (P_{OUT} = 45 W; C_{OUT} = 3 mF)



Figure 3-11. Current Sharing Between Two Devices During Start-up With Short on Output



Figure 3-13. Mismatch (%) in Steady-State Current Sharing in a Four eFuse Parallel Configuration



Figure 3-15. 500-V, 2-Ω Surge Response of Four TPS26631 Devices in Parallel Configuration





Figure 3-16. –500-V, 2-Ω Surge Response of Four TPS26631 Devices in Parallel Configuration

4 Comparison With the Hot-Swap and ORing Controller Solution

In this section, various performance parameters are compared between the eFuse solution and the traditional hot-swap and ORing controllers-based solution for the design specifications tabulated in Table 3-1. Figure 4-1 shows the block diagram of the traditional solution, which uses an LM5069 hot-swap controller with an external FET for inrush current limit, overload, short-circuit, and overvoltage protections and a LM5050 ORing controller with external FET for reverse-current blocking. For more information on the implementation and results of the traditional solution, see the 24-V DC,10-A eFuse and Protection Circuit for Programmable Logic Controllers (PLC) Design Guide.



Figure 4-1. Block Diagram of Hot-Swap and ORing Controllers Based Solution



Table 4-1 details the comparison between the solutions.

Parameter	LM5069 and LM5050 Based Solution	TPS2663 Parallel Configuration	Comments
Input voltage range	9 V to 80 V, 100 V absolute maximum	4.5 V to 60 V, 67 V absolute maximum	Higher absolute maximum voltage rating of LM5069 and LM5050 provides flexibility in high voltage applications.
Driving large capacitive loads	Yes, using dv/dt soft-start circuit at the GATE of LM5069	Yes	The thermal regulation loop in the TPS2663 helps to charge unknown capacitive loads as detailed in the <i>Reliable Startup with Large and Unknown Capactive Loads</i> Application Report.
MOSFET SOA protection	Yes, through the internal FET power-limiting scheme	Yes, through the internal thermal regulation loop and overtemperature protection	Integration offers accurate FET temperature measurement and reliable protection. External FET solution with the LM5069 always overdesigned to account "factor of safety" for FET SOA.
Current limiting (accuracy %)	Yes, (±11.8%)	Yes, (±7%)	Better current limit accuracy with the TPS2663 helps to optimize the input supply size or rating
Current monitoring	No	Analog current monitor output with ±6%	
Surge protection	Provides only Class-B system performance	The fast recovery feature in the TPS2663 helps to achieve Class-A system performance	The LM5069 solution requires large capacitance at the output to buffer the load during surge, power interruptions for meeting Class-A system performance
Supply line transients	Supply line transients cause false trips and often needs trade-off between immunity and short-circuit response	The smart control scheme in the TPS2663 distinguishes real faults from system transients and provides immunity to the transients	
Fault status	No	Yes	Fault status output helps to monitor the system status
No. of components	ICs: LM5069, LM5050 Hot-swap FET: CSD19502Q5B (SON 5 mm × 6 mm) ORing FETs: 2 × CSD19532Q5B (SON 5 mm × 6 mm) R _{SENSE} : 2 mΩ, 1.5 W (6.3 mm × 3 mm) COUT: 7 × 2.2 mF, 35 V (diameter 16 mm)	ICs: 4 × TPS26631 (4 mm × 4 mm) ORing FETs: 2 × CSD19532Q5B (SON 5 mm × 6 mm) COUT: 3 × 1 mF, 35 V (diameter 16 mm)	Only the critical space occupying components are considered. The LM5069 solution requires large output capacitance to meet Class-A system performance.
Solution size	2924 mm ²	1323 mm ²	55% reduction in solution size

Table 4-1. Comparison Between the Solutions



5 TPS16630 Parallel Circuit Configuration

Figure 5-1 shows the parallel circuit configuration for TPS16630 devices. In this circuit, dv/dt start-up is considered, assuming that the system uses a large CdVdT value of > 470 nF where the mismatch in start-up currents between the devices is low. If equal current sharing during start-up is preferred, use the R_{ILIM} switch network at the ILIM pin of each device as discussed in Section 2 for TPS2663 device.



Figure 5-1. Circuit Configuration of 'N' TPS16630 Devices in Parallel



6 Conclusion

The TPS2663 parallel configuration helps to scale up the circuit protection to higher current levels. This approach facilitates a reliable and space-efficient high-current protection solution with the inherent ability to meet Class-A system performance. The additional benefits of accurate current limiting and immunity to system transients with the TPS2663 device clearly outpaces the legacy hot-swap and ORing controllers based solutions.

7 References

- 1. Texas Instruments, *Achieve 20-A Circuit Protection and Space Efficiency Using Paralleled eFuses* Application Report
- 2. Texas Instruments, 24-V DC,10-A eFuse and Protection Circuit for Programmable Logic Controllers (PLC) Design Guide
- 3. Texas Instruments, *Reliable Startup with Large and Unknown Capactive Loads* Application Report
- 4. Texas Instruments, TPS2663x 60-V, 6-A Power Limiting, Surge Protection Industrial eFuse Data Sheet
- 5. Texas Instruments, TPS1663x 60-V, 6-A eFuse with Adjustable Output Power Limiting Data Sheet

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2022, Texas Instruments Incorporated